



1MBI 200N-120

1-Pack IGBT
1200 V
200 A

IGBT MODULE (N series)

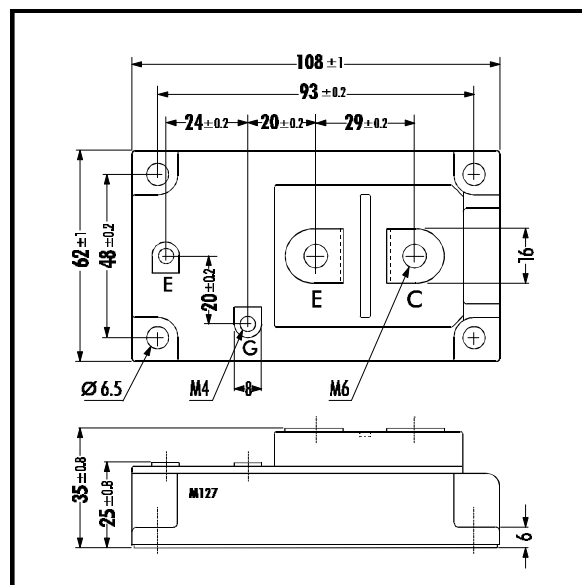
Features

- Square RBSOA
- Low Saturation Voltage
- Less Total Power Dissipation
- Improved FWD Characteristic
- Minimized Internal Stray Inductance
- Overcurrent Limiting Function (4-5 Times Rated Current)

Applications

- High Power Switching
- A.C. Motor Controls
- D.C. Motor Controls
- Uninterruptible Power Supply

Outline Drawing



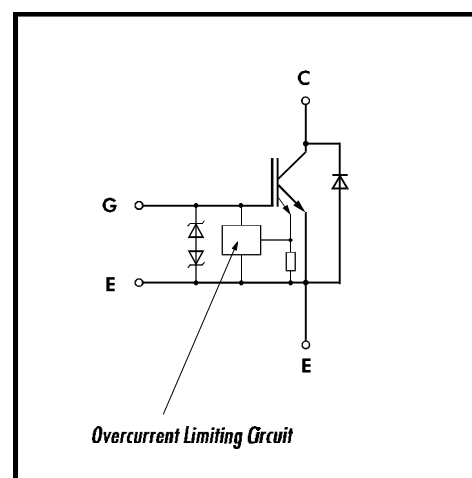
Maximum Ratings and Characteristics

Absolute Maximum Ratings (T_c=25°C)

Items	Symbols	Ratings	Units
Collector-Emitter Voltage	V _{CES}	1200	V
Gate -Emitter Voltage	V _{GES}	± 20	V
Collector Current	Continuous	I _C	200
	1ms	I _{C PULSE}	400
	Continuous	-I _C	200
	1ms	-I _{C PULSE}	400
Max. Power Dissipation	P _C	1500	W
Operating Temperature	T _i	+150	°C
Storage Temperature	T _{stg}	-40 ~ +125	°C
Isolation Voltage	V _{is}	2500	V
Screw Torque	Mounting *1	3.5	Nm
	Terminals *2	4.5	
	Terminals *3	1.7	

Note: *1:Recommendable Value; 2.5 - 3.5 Nm (M5) or (M6)
*2:Recommendable Value; 3.5 - 4.5 Nm (M6)
*3:Recommendable Value; 1.3 - 1.7 Nm (M4)

Equivalent Circuit



Electrical Characteristics (at T_f=25°C)

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Zero Gate Voltage Collector Current	I _{CES}	V _{GE} =0V V _{CE} =1200V			4.0	mA
Gate-Emitter Leakage Current	I _{GES}	V _{CE} =0V V _{GE} =± 20V			60	μA
Gate-Emitter Threshold Voltage	V _{GE(th)}	V _{GE} =20V I _C =200mA	4.5		7.5	V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	V _{GE} =15V I _C =200A			3.3	V
Input capacitance	C _{ies}	V _{GE} =0V V _{CE} =10V f=1MHz		32000		pF
Output capacitance	C _{oes}			11600		
Reverse Transfer capacitance	C _{res}			10320		
Turn-on Time	t _{ON}	V _{CC} =600V I _C =200A		0.65	1.2	μs
	t _r			0.25	0.6	
Turn-off Time	t _{OFF}	V _{GE} =± 15V		0.85	1.5	μs
	t _f	R _G =4.7Ω		0.35	0.5	
Diode Forward On-Voltage	V _F	I _F =200A V _{GE} =0V			3.0	V
Reverse Recovery Time	t _{rr}	I _F =200A			350	ns

Thermal Characteristics

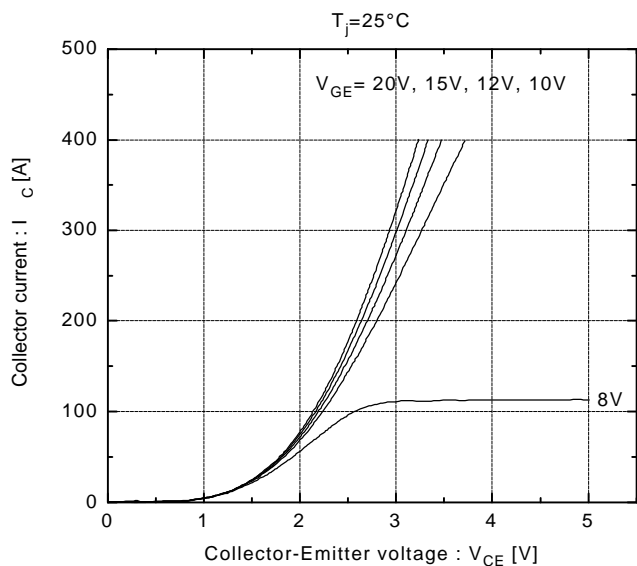
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	R _{th(f-c)}	IGBT			0.085	°C/W
	R _{th(f-c)}	Diode			0.22	
	R _{th(c-f)}	With Thermal Compound		0.0125		



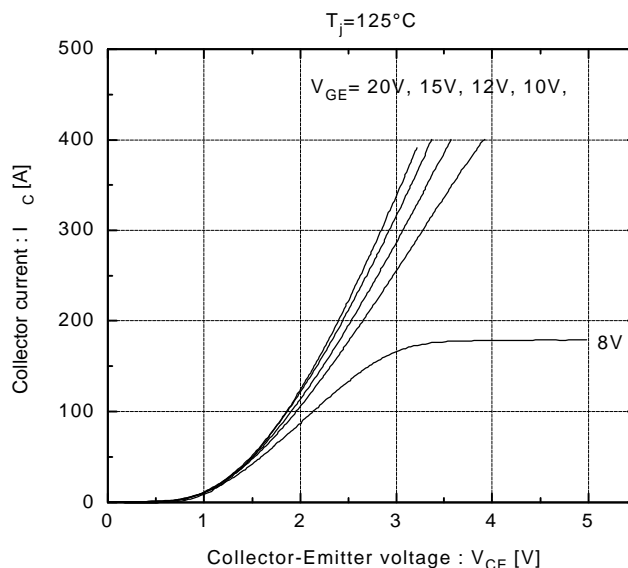
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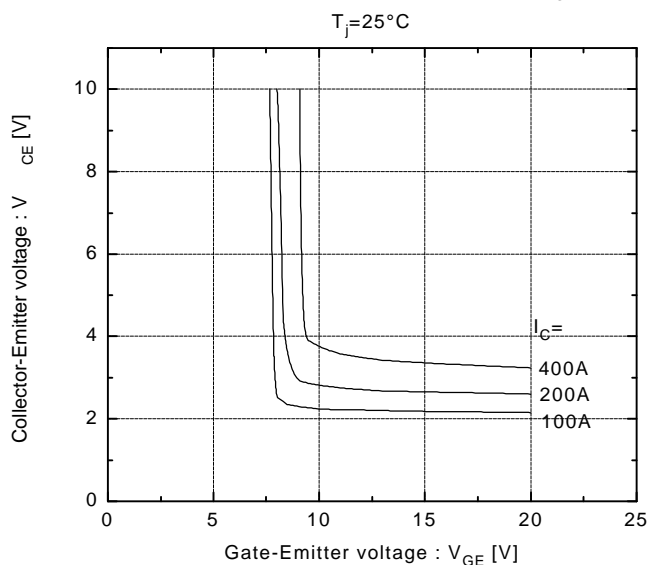
Collector current vs. Collector-Emittor voltage



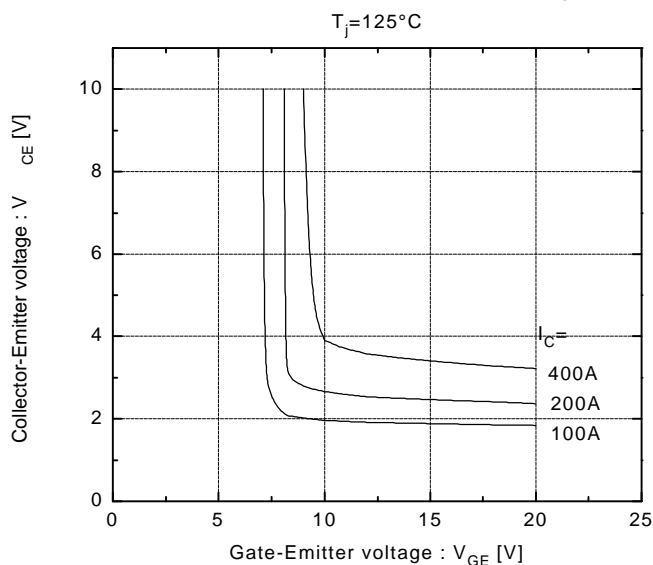
Collector current vs. Collector-Emittor voltage



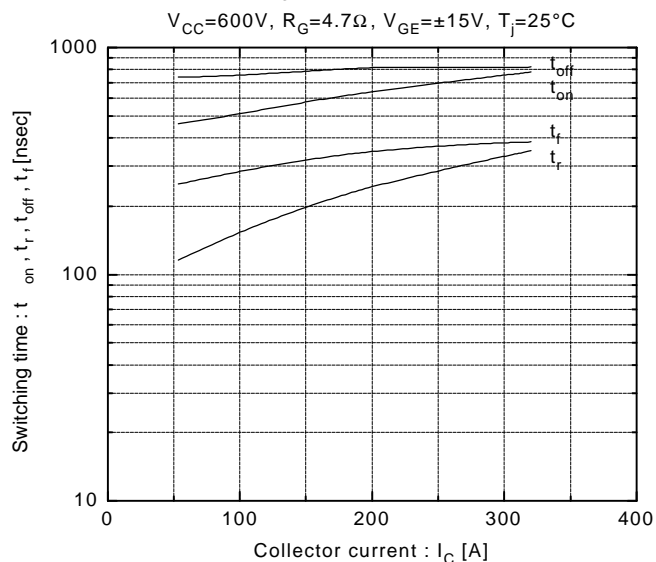
Collector-Emittor vs. Gate-Emittor voltage



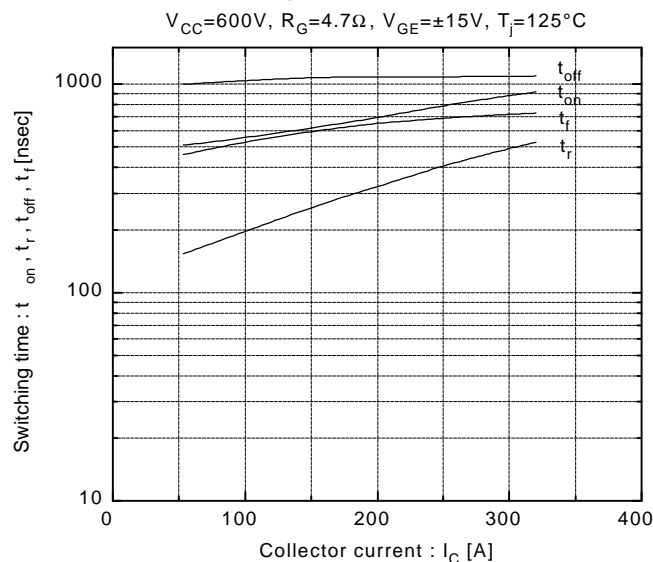
Collector-Emittor vs. Gate-Emittor voltage



Switching time vs. Collector current



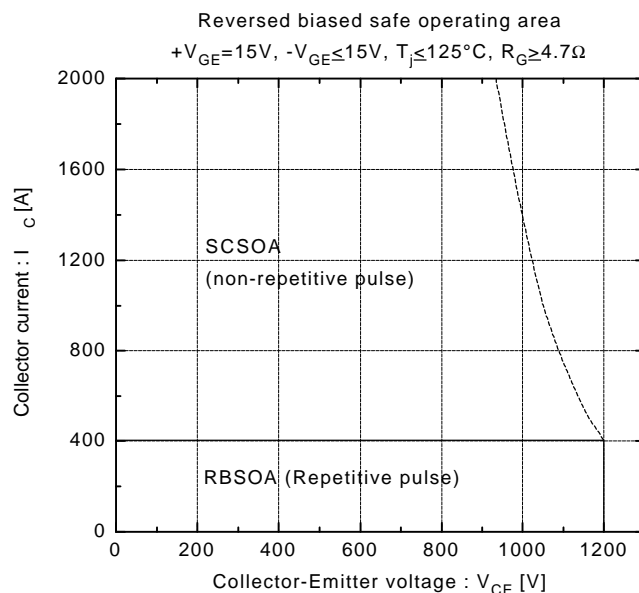
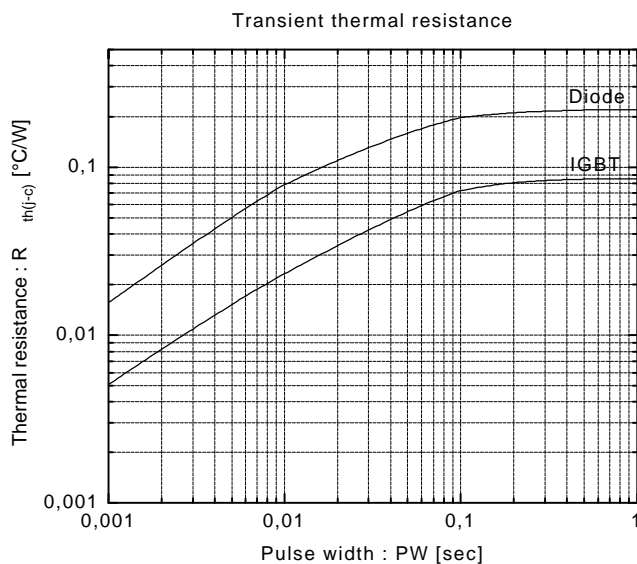
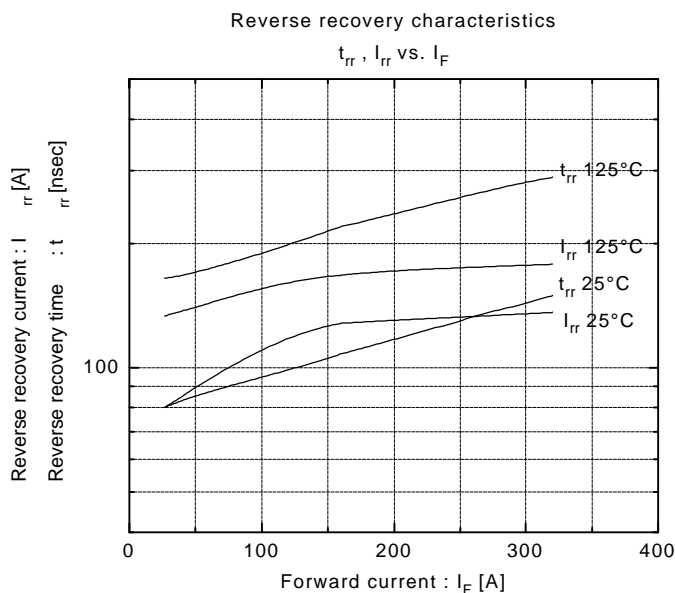
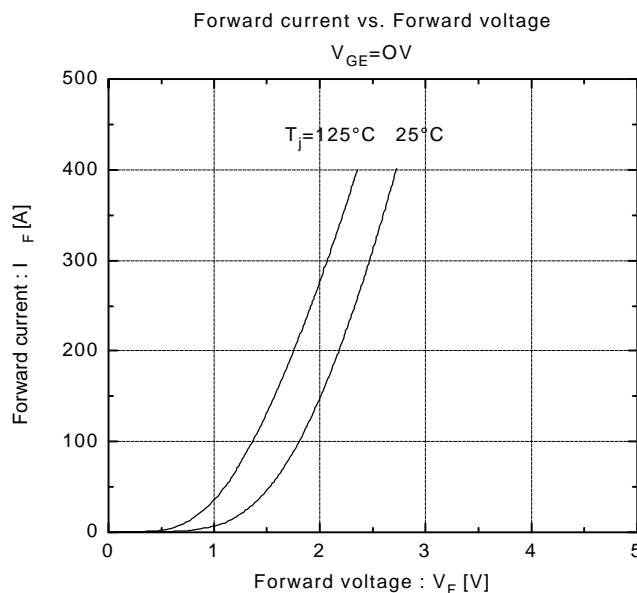
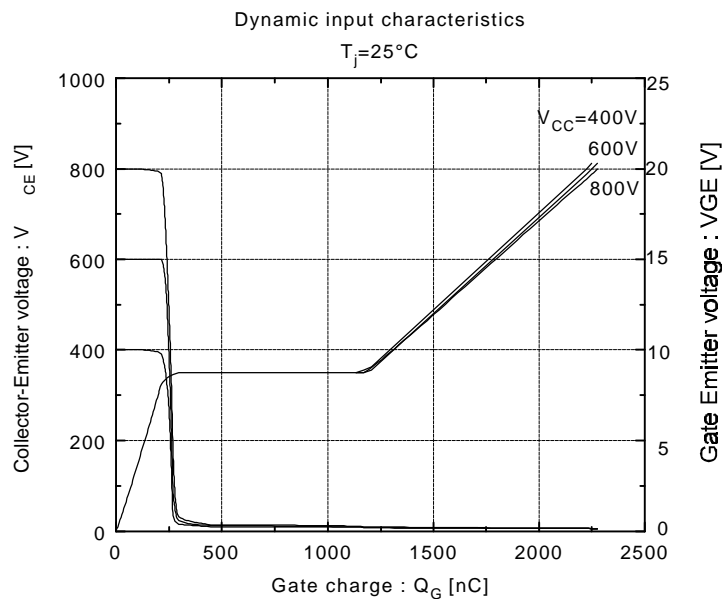
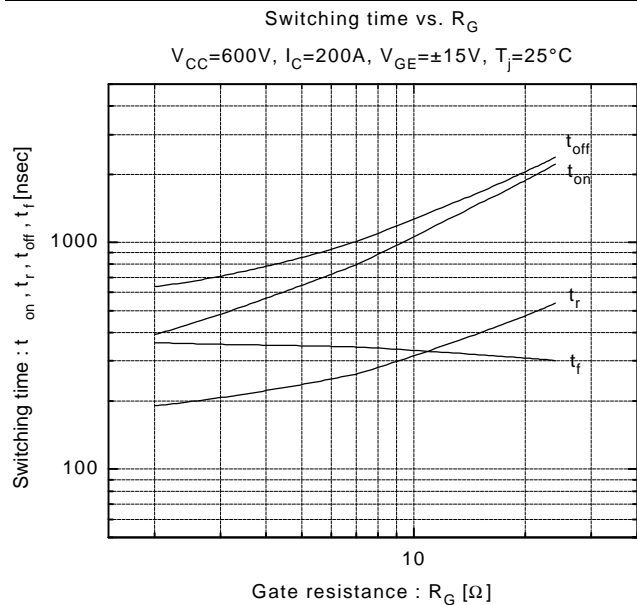
Switching time vs. Collector current





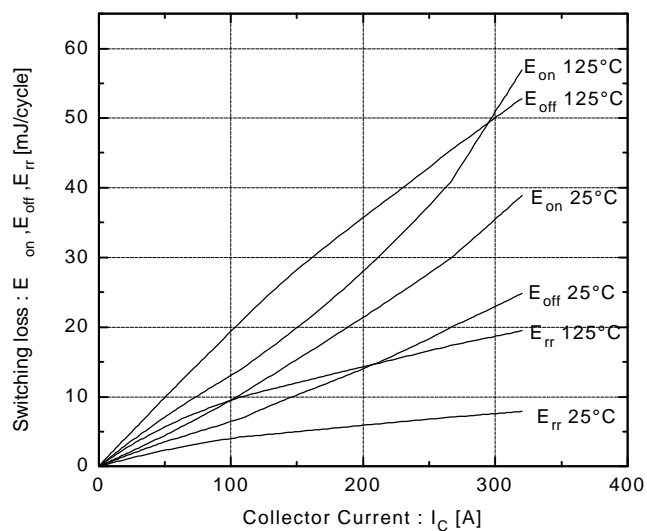
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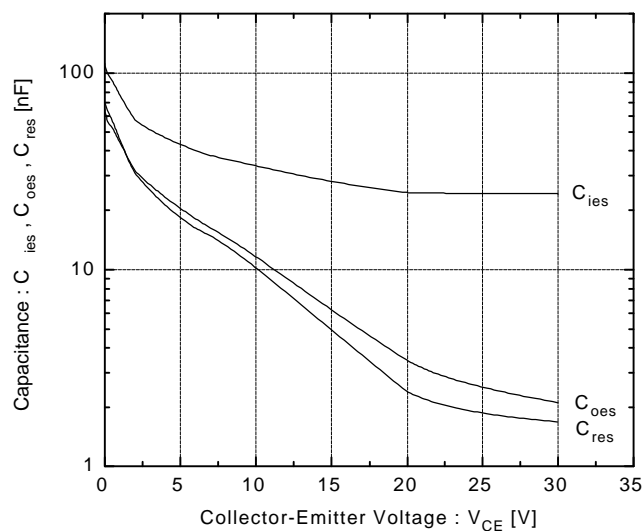


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ELECTRIC**1MBI 200N-120****1-Pack IGBT**
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Switching loss vs. Collector current

 $V_{CC}=600V$, $R_G=4.7\Omega$, $V_{GE}=\pm 15V$ 

Capacitance vs. Collector-Emitter voltage

 $T_j=25^\circ C$ **Fuji Electric GmbH**

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